Amendm nts to the Sp cification

Please insert the following two new paragraphs starting at line 17 on page 3:

Fig. 7 is an alternate embodiment to that depicted by Fig. 3.

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Fig. 8 is an alternate embodiment to that depicted by Fig. 4.

Please amend the paragraph beginning at line 4 on page 7 as follows:

Referring to Fig. 4, an insulative layer 36 is formed over the substrate, with an example being borophosphosilicate glass (BPSG) deposited to a thickness of 10,000 Angstroms. Such provides but one example of providing insulative material which is received proximate gate 26. Layer 36 is preferably planarized, as shown. An opening 38 is formed into insulative layer 36, and all the way to a conductive portion of gate 26, as shown. Semiconductive material conductively doped with a conductivity enhancing impurity opposite in type to that used to dope material 16 is formed within the opening. A preferred technique is chemical vapor deposition with *in situ* doping, followed by planarization such as chemical-mechanical polishing to produce the illustrated plug 40 of semiconductive material within opening 38. Such provides but one example of providing conductively doped semiconductive material within electrically insulative material 36, which is proximate gate 36, and in electrical connection with gate 36. Conductive diffusion barrier layer 20 of gate 26 is accordingly received between or intermediate semiconductive material 16 of gate 26 and semiconductive material 40 within opening 38. Fig. 4 illustrates plugging material 40 as comprising p+ doped material, with the semiconductive polysilicon material of layer 16 being n+ doped.

Such could of course be reversed. Alternately, the conductivity types could be the same. Further considered, silicide layer 18 might not be included in certain aspects of the invention (for example as shown in Figs. 7 and 8 with respect to a wafer fragment 10b), which is intended only to be limited by the accompanying claims appropriately interpreted in accordance with the Doctrine of Equivalents. Where a silicide layer is utilized, preferably the silicide layer and conductive diffusion barrier layer comprise a common metal. For example where the silicide is WSi_x, a preferred barrier layer material is one or more of W_xN_y and TiW_xN_y. Where the silicide layer is $TiSi_x$, a preferred barrier layer material is one or more of TiN, TiO_xN_y, and TiW_xN_y. The barrier layer and silicide layer are preferably deposited in the same chamber.

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